

N-Channel Power MOSFET

700V, 3A, 1.4Ω

FEATURES

- Super-Junction technology
- High performance, small $R_{DS(ON)} * Q_g$ figure of merit (FOM)
- High ruggedness performance
- 100% UIS and R_g tested
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	700	V
$R_{DS(on)}$ (max)	1.4	Ω
Q_g	7.4	nC

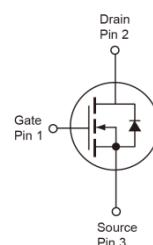
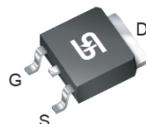
APPLICATION

- Power Supply
- AC/DC LED Lighting



✓
RoHS
COMPLIANT
HALOGEN
FREE

TO-252 (DPAK)



Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	700	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ^(Note 1)	I_D	3	A
$T_C = 100^\circ\text{C}$		1.8	
Pulsed Drain Current ^(Note 2)	I_{DM}	9	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	28	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	26	mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	0.6	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\Theta JC}$	4.4	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	BV_{DSS}	700	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	2	--	4	V
Gate Body Leakage	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700\text{V}$, $V_{GS} = 0\text{V}$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance (Note 4)	$V_{GS} = 10\text{V}$, $I_D = 1.2\text{A}$	$R_{DS(\text{ON})}$	--	1.1	1.4	Ω
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 380\text{V}$, $I_D = 3\text{A}$, $V_{GS} = 10\text{V}$	Q_g	--	7.4	--	nC
Gate-Source Charge		Q_{gs}	--	1.8	--	
Gate-Drain Charge		Q_{gd}	--	2.4	--	
Input Capacitance	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	C_{iss}	--	317	--	pF
Output Capacitance		C_{oss}	--	42	--	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	--	3.2	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380\text{V}$, $R_{\text{GEN}} = 25\Omega$, $I_D = 3\text{A}$, $V_{GS} = 10\text{V}$,	$t_{d(\text{on})}$	--	16	--	ns
Turn-On Rise Time		t_r	--	15	--	
Turn-Off Delay Time		$t_{d(\text{off})}$	--	26	--	
Turn-Off Fall Time		t_f	--	8	--	
Source-Drain Diode						
Forward On Voltage (Note 4)	$I_S = 3\text{A}$, $V_{GS} = 0\text{V}$	V_{SD}	--	--	1.4	V
Reverse Recovery Time	$V_R = 200\text{V}$, $I_S = 2\text{A}$ $dI_F/dt = 100\text{A}/\mu\text{s}$	t_{rr}	--	137	--	ns
Reverse Recovery Charge		Q_{rr}	--	0.7	--	μC

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 144\text{mH}$, $I_{AS} = 0.6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

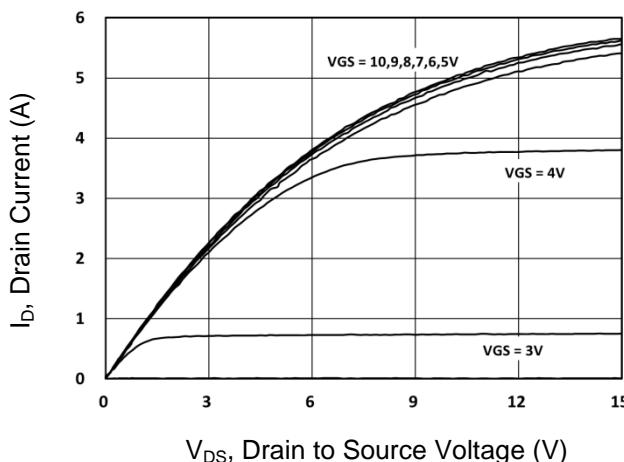
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM70NB1R4CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

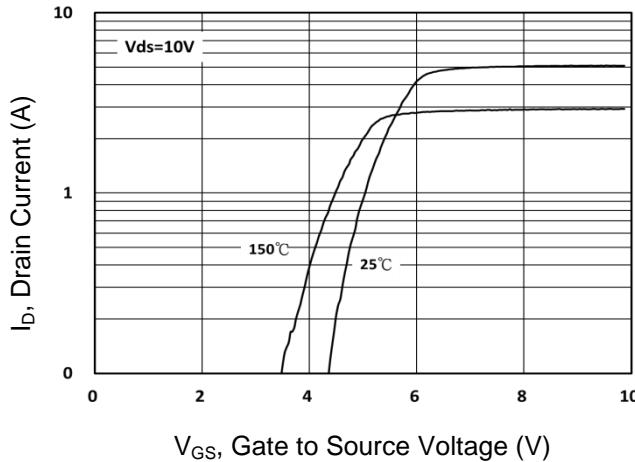
CHARACTERISTICS CURVES

($T_c = 25^\circ\text{C}$ unless otherwise noted)

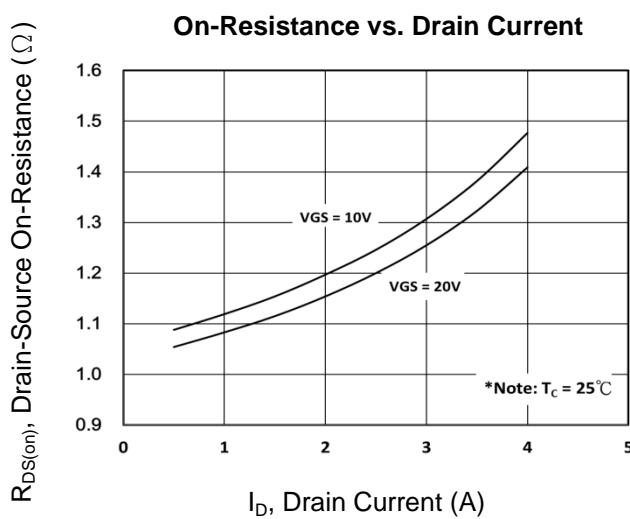
Output Characteristics



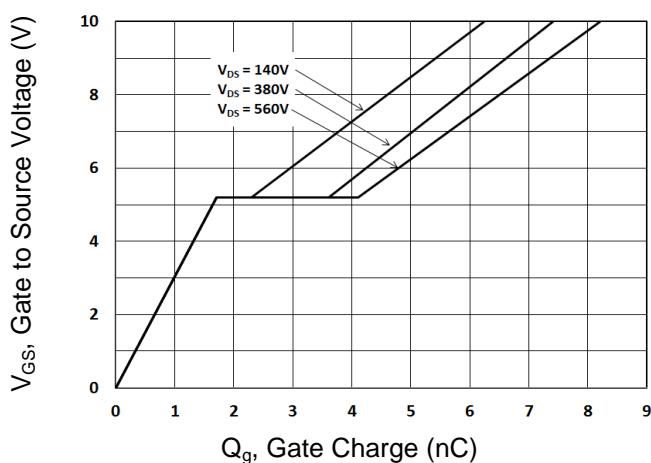
Transfer Characteristics



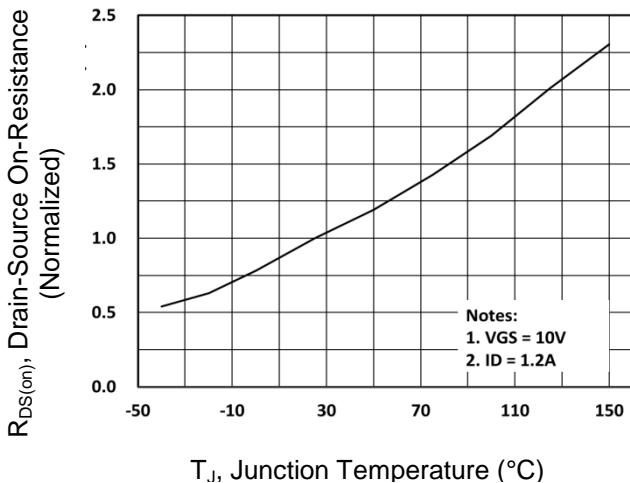
On-Resistance vs. Drain Current



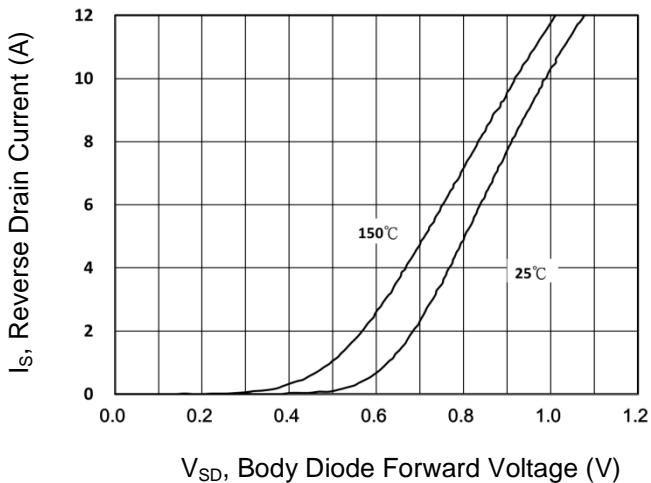
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature

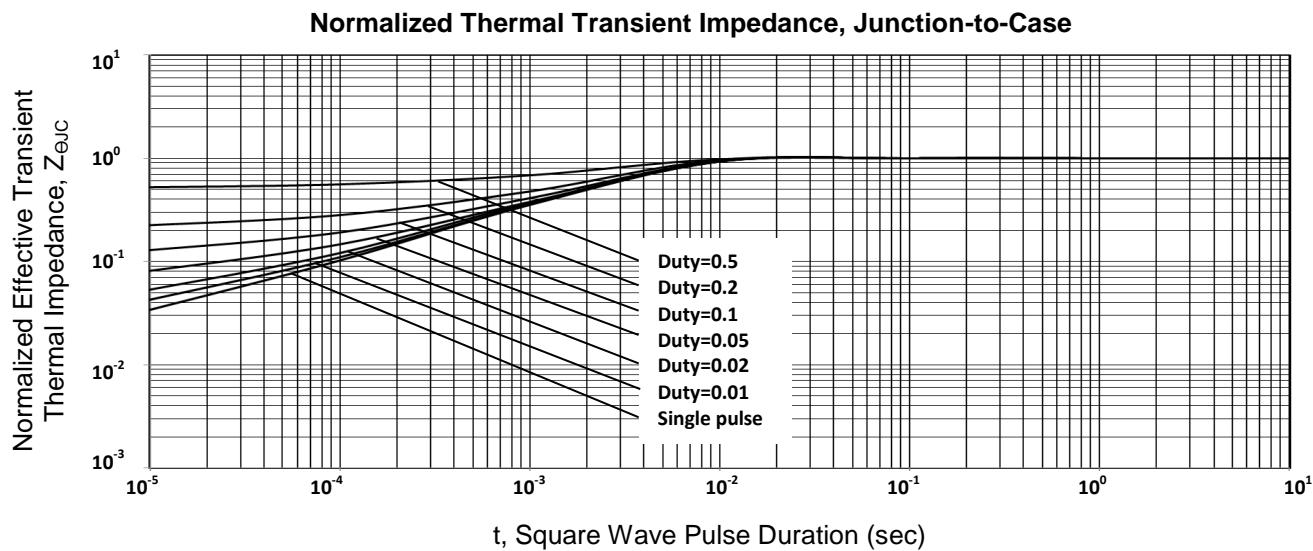
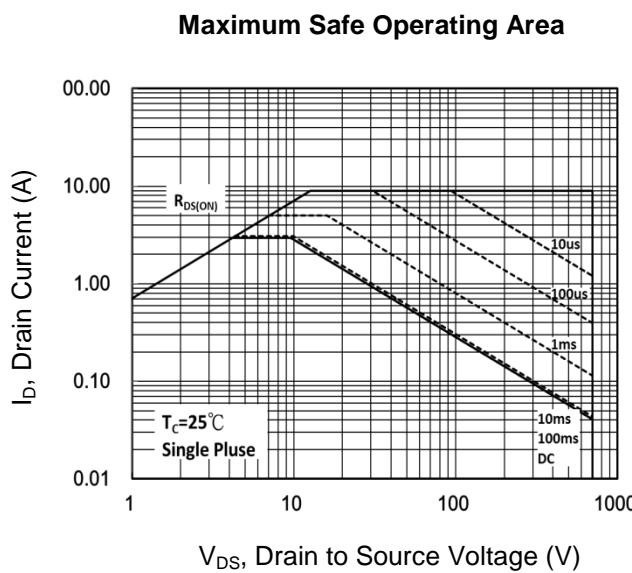
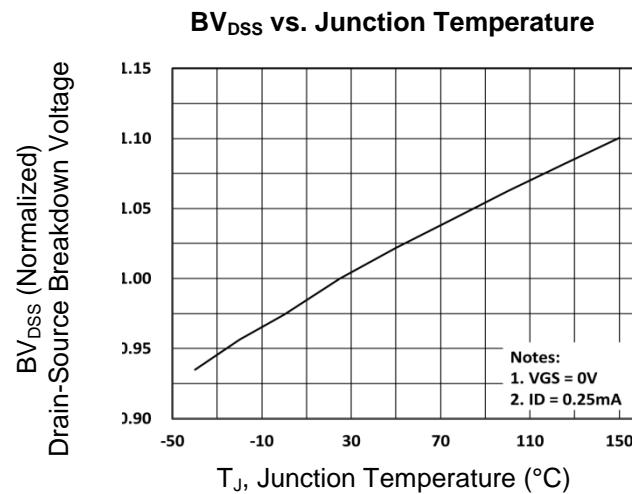
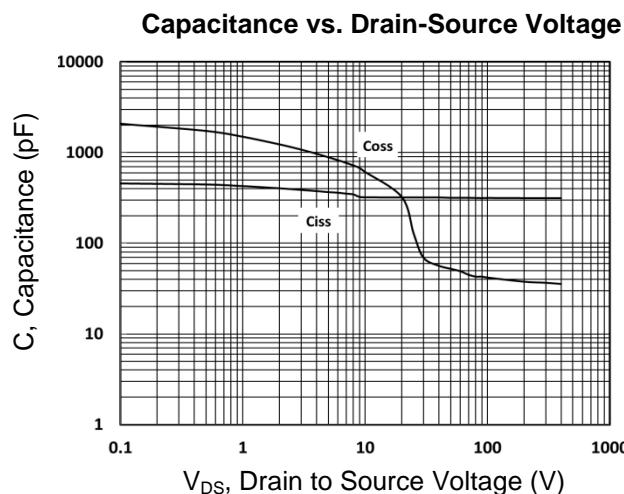


Source-Drain Diode Forward Current vs. Voltage

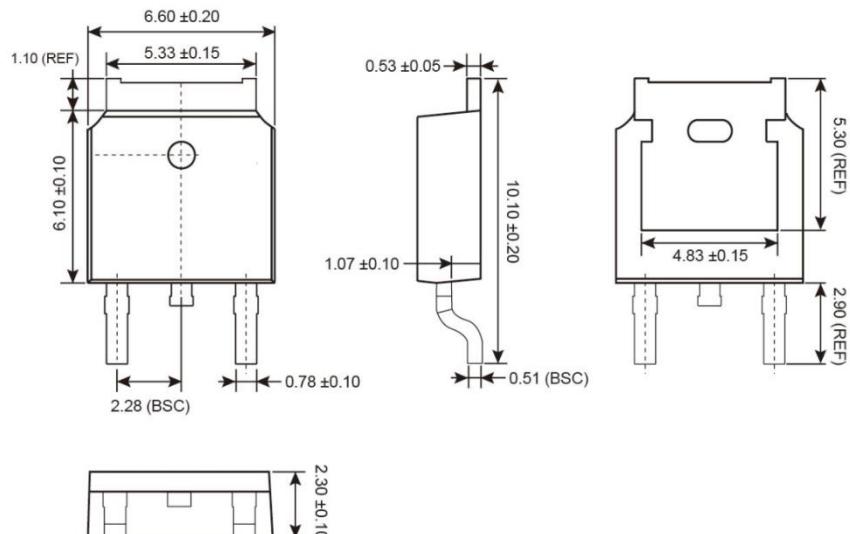
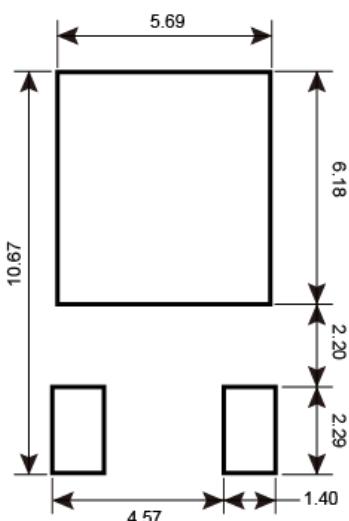


CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-252

SUGGESTED PAD LAYOUT

MARKING DIAGRAM

Y = Year Code

M = Month Code

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code (1~9, A~Z)

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